
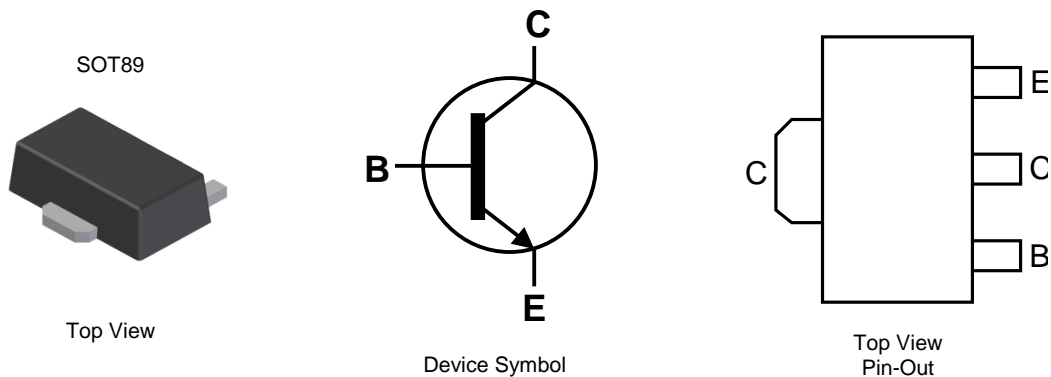


**Features**

- $BV_{CEO} > 40V$
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (DXT3906)
- Ideal for Medium Power Switching or Amplification Applications
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight: 0.072 grams (Approximate)

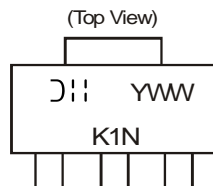


**Ordering Information** (Note 4)

Part Number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DXT3904-13	AEC-Q101	K1N	13	12	2,500

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
  3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**



K1N = Product Type Marking Code  
 YWW = Date Code Marking  
 Y = Last Digit of Year ex: 4 = 2014  
 WW = Week Code 01 - 52

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current – Continuous	I <sub>C</sub>	200	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation	(Note 5)	0.75	W
	(Note 6)	1.2	
Thermal Resistance, Junction to Ambient Air	(Note 5)	166	°C/W
	(Note 6)	104	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**ESD Ratings** (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
5. For a device mounted with the exposed collector pad on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  6. Same as note (5), except the device is mounted with the exposed collector pad on 25mm x 25mm 1oz copper.
  7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>					
Collector-Base Breakdown Voltage	$BV_{CBO}$	60	—	V	$I_C = 10\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	40	—	V	$I_C = 1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	6.0	—	V	$I_E = 10\mu\text{A}, I_C = 0$
Collector Cutoff Current	$I_{CEX}$	—	50	nA	$V_{CE} = 30\text{V}, V_{EB(OFF)} = 3.0\text{V}$
Base Cutoff Current	$I_{BL}$	—	50	nA	$V_{CE} = 30\text{V}, V_{EB(OFF)} = 3.0\text{V}$
<b>ON CHARACTERISTICS (Note 7)</b>					
DC Current Gain	$h_{FE}$	40	—	—	$I_C = 100\mu\text{A}, V_{CE} = 1.0\text{V}$ $I_C = 1.0\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 10\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 50\text{mA}, V_{CE} = 1.0\text{V}$ $I_C = 100\text{mA}, V_{CE} = 1.0\text{V}$
		70	—		
		100	300		
		60	—		
		30	—		
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.20 0.30	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.65	0.85 0.95	V	$I_C = 10\text{mA}, I_B = 1.0\text{mA}$ $I_C = 50\text{mA}, I_B = 5.0\text{mA}$
<b>SMALL SIGNAL CHARACTERISTICS</b>					
Output Capacitance	$C_{obo}$	—	4.0	pF	$V_{CB} = 5.0\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	$C_{ibo}$	—	8.0	pF	$V_{EB} = 0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Input Impedance	$h_{ie}$	1.0	10	k $\Omega$	$V_{CE} = 10\text{V}, I_C = 1.0\text{mA}, f = 1.0\text{kHz}$
Voltage Feedback Ratio	$h_{re}$	0.5	8.0	$\times 10^{-4}$	
Small Signal Current Gain	$h_{fe}$	100	400	—	
Output Admittance	$h_{oe}$	1.0	40	$\mu\text{S}$	
Current Gain-Bandwidth Product	$f_T$	300	—	MHz	
Noise Figure	NF	—	5.0	dB	$V_{CE} = 5.0\text{V}, I_C = 100\mu\text{A}, R_S = 1.0\text{k}\Omega, f = 1.0\text{kHz}$
<b>SWITCHING CHARACTERISTICS</b>					
Delay Time	$t_d$	—	35	ns	$V_{CC} = 3.0\text{V}, I_C = 10\text{mA},$
Rise Time	$t_r$	—	35	ns	$V_{BE(off)} = -0.5\text{V}, I_{B1} = 1.0\text{mA}$
Storage Time	$t_s$	—	200	ns	$V_{CC} = 3.0\text{V}, I_C = 10\text{mA},$
Fall Time	$t_f$	—	50	ns	$I_{B1} = -I_{B2} = 1.0\text{mA}$

Notes: 7. Measured under pulsed condition. Pulse width = 300 $\mu\text{s}$ . Duty cycle  $\leq 2\%$ .

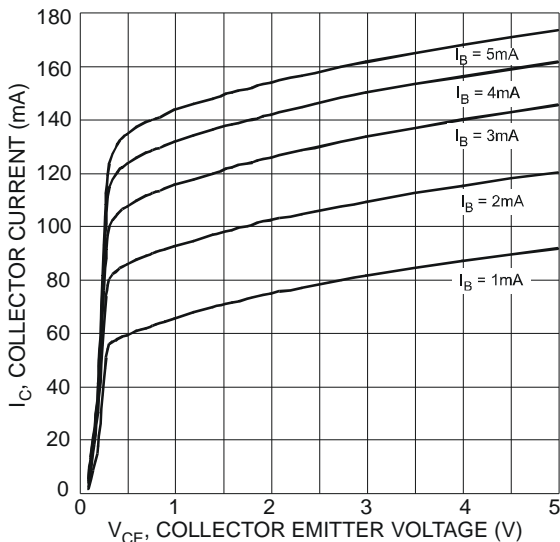


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage

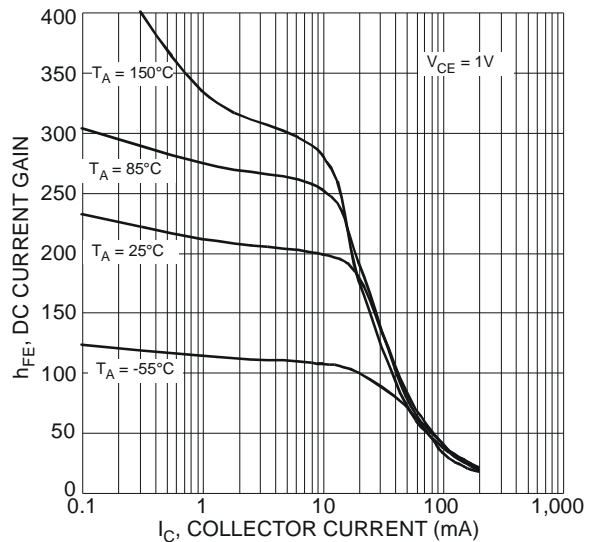


Fig. 3 Typical DC Current Gain vs. Collector Current

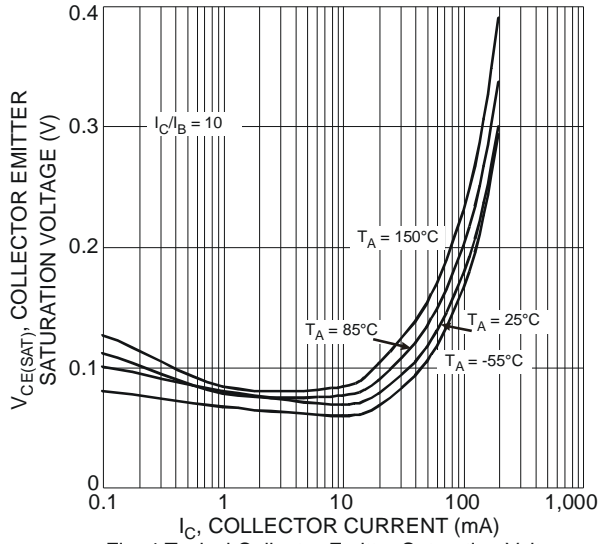


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

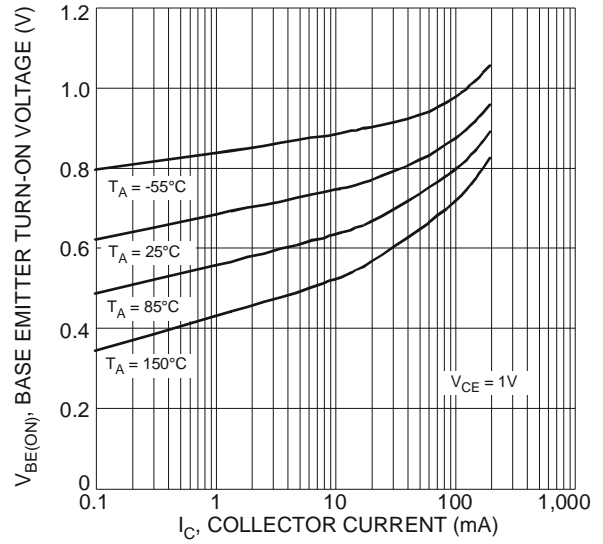


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

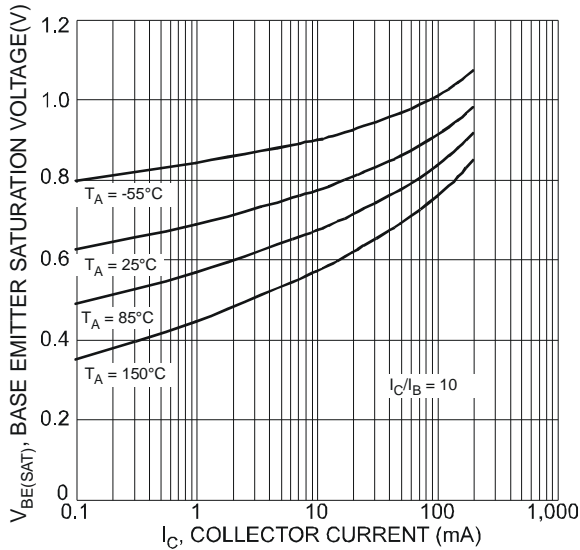


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

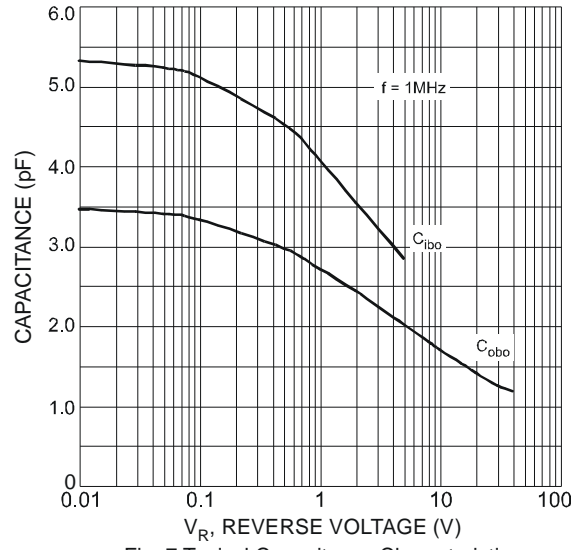


Fig. 7 Typical Capacitance Characteristics

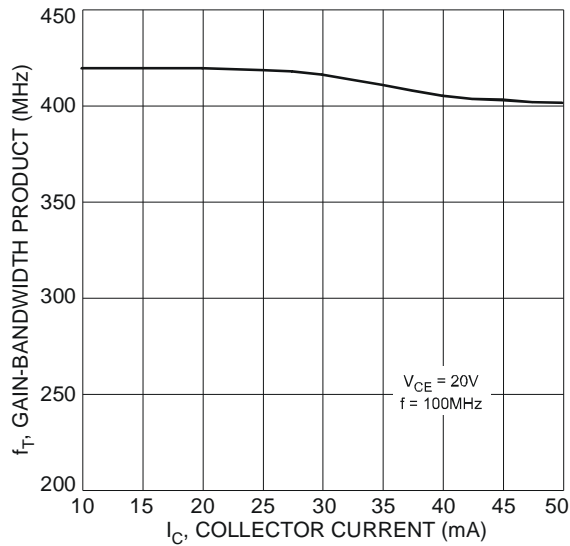
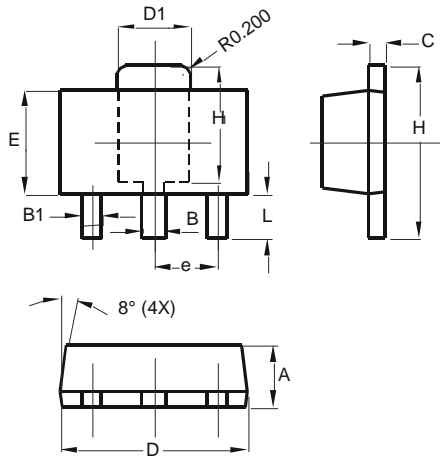


Fig. 8 Typical Gain-Bandwidth Product vs. Emitter Current

**Package Outline Dimensions**

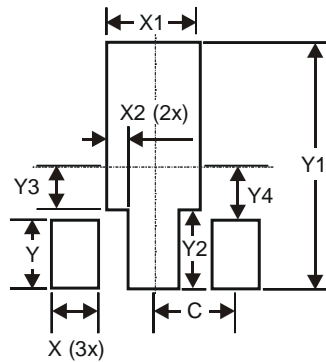
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT89		
Dim	Min	Max
A	1.40	1.60
B	0.44	0.62
B1	0.35	0.54
C	0.35	0.44
D	4.40	4.60
D1	1.62	1.83
E	2.29	2.60
e	1.50 Typ	
H	3.94	4.25
H1	2.63	2.93
L	0.89	1.20
<b>All Dimensions in mm</b>		

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
C	1.500

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